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B. Amendments to the Specification.

Please replace the paragraph beginning on Page 3, Line 8 with the following.

5 A drawback to a conventional method 500 can be how such a cleaning method affects chamber part surfaces. For example, chamber parts can typically be formed from quartz. A wet clean of H_2O_2 and NH_2OH may etch quartz surfaces changing surface textures. Changes in chamber part surfaces may result in drift in an etch process, as a changing surface conditions may alter gas flows and or etch chemistry. Further, because cleaning may consume etch chamber parts, 10 such parts may have to be periodically replaced.

Please replace the paragraph beginning on Page 6, Line 20 with the following.

Referring now to FIG. 2, a second embodiment is disclosed in a flow diagram. A second 15 embodiment is designated by the general reference character 200 and may include a plasma clean (step 202). A step 202 may include plasma cleaning chamber parts with a recipe that is highly selective between plasma a chamber part and a material that has been redistributed on such a chamber part. Such a selectivity can be greater than 1:100.

20 Please replace the paragraph beginning on Page 8, Line 15 with the following.

Plasma cleaning with oxygen as a source gas (also referred to "ashing") can remove organic based materials, such a polymer-based photoresist. At the same time, an oxygen plasma etch can leave quartz surfaces essentially unaltered. In this way, unlike conventional cleaning 25 methods that may consume quartz material in an H_2O_2 and NH_2OH dip, a third embodiment 300 may clean quartz material with a solvent and/or plasma clean that consumes essentially no quartz

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

C3 material. For example, a selectivity between a quartz material and an organic based material can be greater than 1:100.

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